



April 7, 2004

TO: Commissioner for Patents
P.O.Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
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Subject: | Serial No. 10/689,421 10/20/03 |

Denny D. Tang et al.

REFERENCE GENERATOR FOR MULTILEVEL
NONLINEAR RESISTIVITY MEMORY
STORAGE ELEMENTS

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
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Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 4/12/04

TSMC-02-818

A translation of the abstract of Taiwan Patent 518597 is attached:

Taiwan Patent 518597, "MRAM-arrangement," discusses a MRAM-arrangement, in which a switch-transistor is arranged respectively to several TMR-memory cells.

Sincerely,

A handwritten signature in black ink, appearing to read 'S. B. Ackerman', with a long horizontal flourish extending to the right.

Stephen B. Ackerman,
Reg. No. 37761

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION.

APR 15 2004

(Use several sheets if necessary)

Director's Number (Optional)	Application Number
TSMC-02-818	10/689,421
Applicant Denny D. Tang et al.	
Filing Date 10/20/03	Group Art Unit

[illegible][illegible][illegible]

DATE COMPLETED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.